

Title (en)
JUNCTION LASER

Publication
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Application
EP 78200074 A 19780703

Priority
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Abstract (en)
[origin: EP0000412A2] A semiconductor laser or traveling wave intensifier having an active layer between two passive semiconductor layers, and a strip-shaped electrode geometry. According to the invention the active layer is uniform in thickness. while at least one of the passive layers within the strip-shaped geometry comprises a strip-shaped zone of deviating construction and is built up from portions having different refractive indices n , and $n_{₂}$. According to the invention it holds thatwherein n , is the refractive index of the portion which at least within said strip-shaped zone adjoins the active layer, d , is the thickness thereof within the strip-shaped zone, and $d_{₂}$ is the thickness thereof beside the strip-shaped zone.

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